

SOT-23 Plastic-Encapsulate Transistors

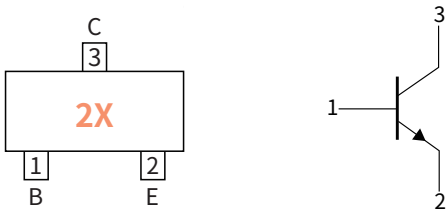
Features

- Complementary to MMBT4403
- Power dissipation of 300mW
- High stability and high reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260°C

Mechanical Data

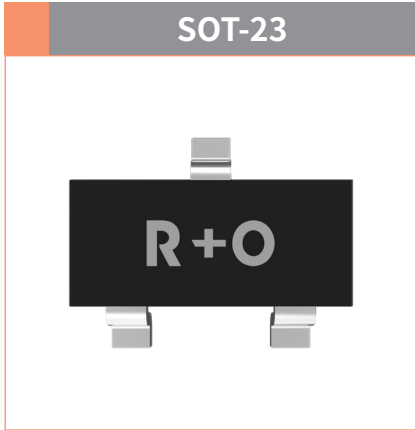
- Case: SOT-23
- Molding compound meets UL 94V-0 flammability rating, RoHS-compliant,halogen-free
- Terminals: Solder plated, solderable per MIL-STD-750,Method 2026

Function Diagram



Collector-Base Voltage
VCBO 60V

Collector Current
0.6 Ampere



PARAMETER	SYMBOL	UNIT	VALUE
Collector-Base Voltage	V_{CBO}	V	60
Collector-Emitter Voltage	V_{CEO}		40
Emitter-Base Voltage	V_{EBO}		6.0
Collector Current	I_C	mA	600
Collector Power Dissipation	P_C	mW	300
Storage temperature	T_{stg}	°C	-55 ~+150
Junction temperature	T_j	°C	-55 ~+150
Typical Thermal Resistance	$R_{\theta J-A}$	°C /W	417

Small-signal Characteristics

ITEM	SYMBOL	Condition	UNIT	Min	Max
Transition frequency	f_T	$I_C=20mA, V_{CE}=10V, f=100MHz$	MHz	250	—

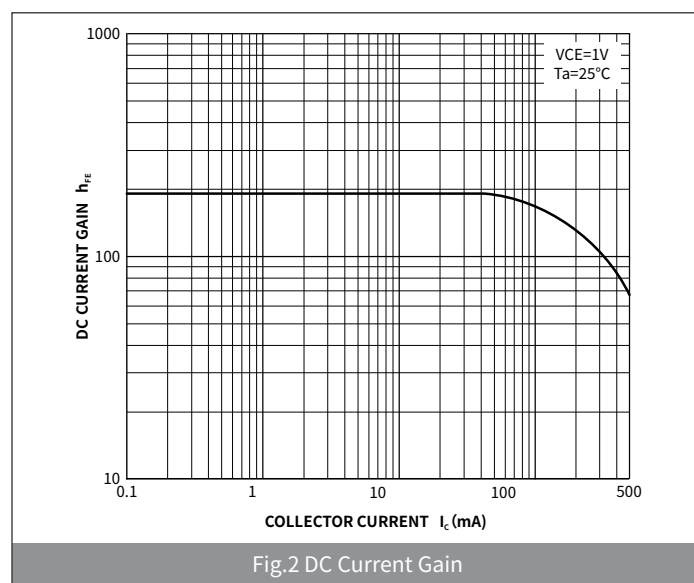
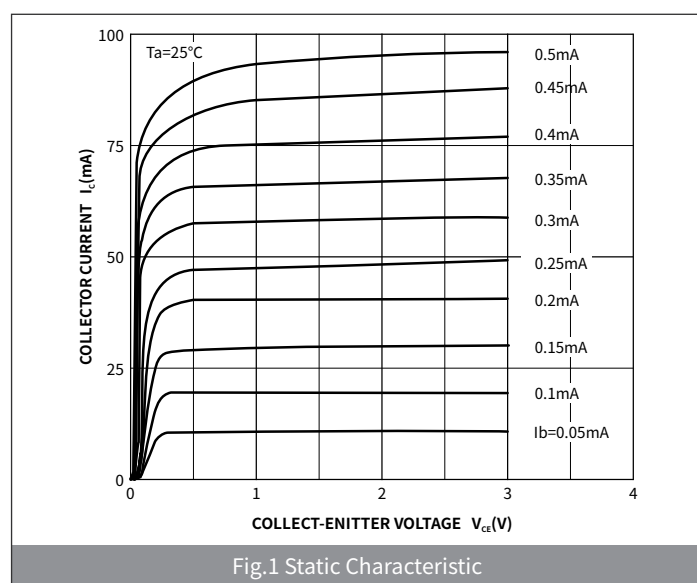
Ordering Information

PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	120000	7"

● **Electrical Characteristics** (Ta=25°C Unless otherwise noted)

PARAMETER	SYMBOL	UNIT	Condition	Min	Max
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V	$I_C=100\mu A, I_E=0$	60	—
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$		$I_C=1.0mA, I_B=0$	40	—
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$		$I_E=100\mu A, I_C=0$	6.0	—
Collector-Base cut-off current	I_{CBO}	nA	$V_{CB}=50V, I_E=0$	—	100
Collector cut-off current	I_{CEO}		$V_{CE}=35V, V_{EB(off)}=0.4V$	—	100
Emitter-Base cut-off current	I_{EBO}		$V_{EB}=5.0V, I_C=0$	—	100
DC Current Gain	h_{FE}	—	$I_C=0.1mA, V_{CE}=1.0V$	20	—
			$I_C=1.0mA, V_{CE}=1.0V$	40	—
			$I_C=10mA, V_{CE}=1.0V$	80	—
			$I_C=150mA, V_{CE}=1.0V$	100	300
			$I_C=500mA, V_{CE}=1.0V$	40	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	V	$I_C=150mA, I_B=15mA$	—	0.4
Collector-Emitter Saturation Voltage	$V_{CE(sat)2}$		$I_C=50mA, I_B=50mA$	—	0.75
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$		$I_C=150mA, I_B=15mA$	—	0.95
Base-Emitter Saturation Voltage	$V_{BE(sat)2}$		$I_C=50mA, I_B=50mA$	—	1.2
Delay time	t_d	ns	$V_{CE}=30V, V_{BE(off)}=2.0V$ $I_C=150mA, I_{B1}=15mA$	—	15
Rise time	t_r			—	20
Storage time	t_s		$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$	—	225
Fall time	t_f			—	60

● **Ratings And Characteristics Curves** (Ta=25°C Unless otherwise specified)



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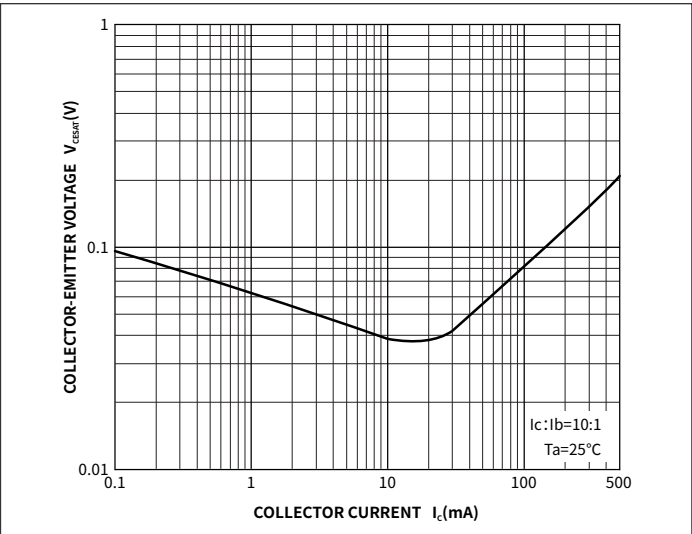


Fig.3 Collector-Emitter Saturation Voltage

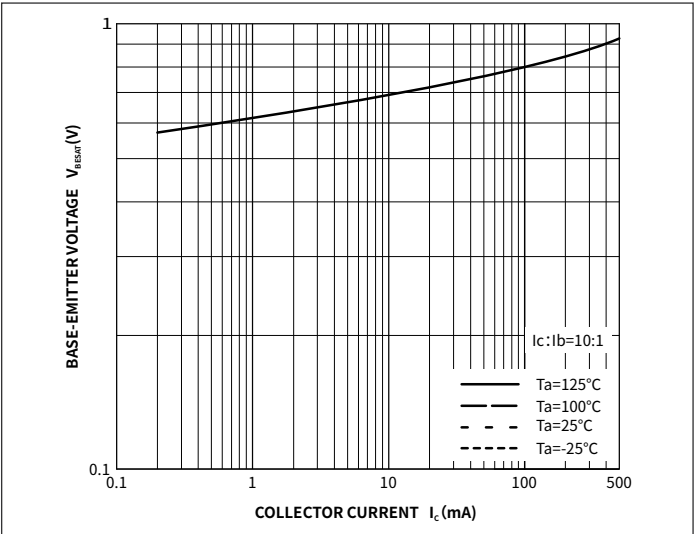


Fig.4 Base-Emitter Saturation Voltage

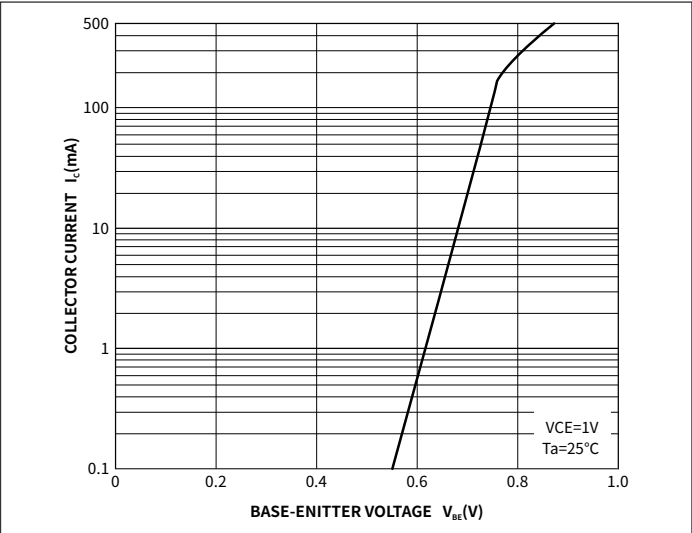


Fig.5 Base-Emitter On Voltage

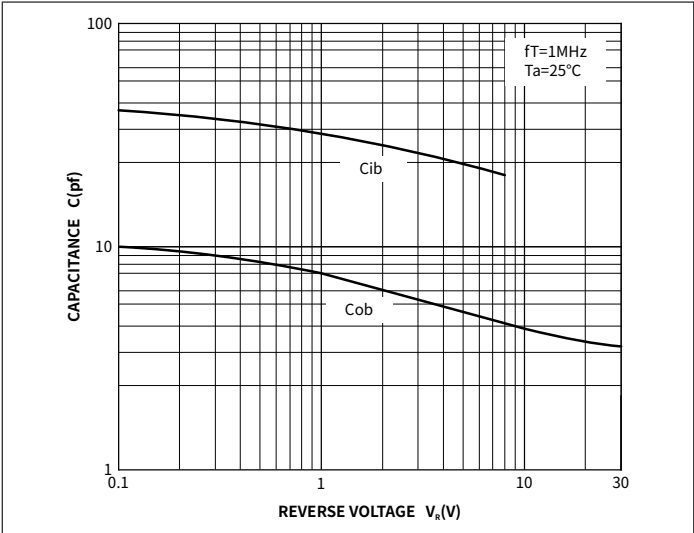
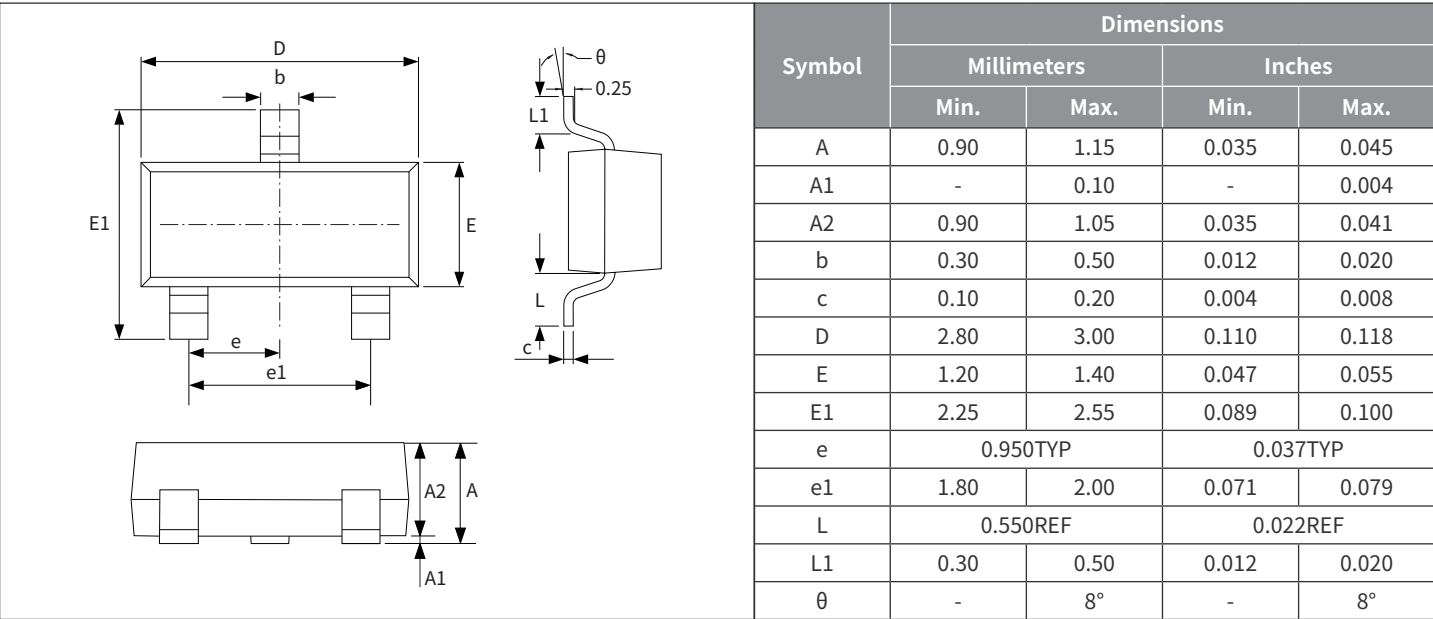


Fig.6 $C_{ob}/C_{ib}-V_C V_{EB}$

● Package Outline Dimensions (SOT-23)



● Suggested Pad Layout

